ANMI027035-P40

S-band matched GaN power amplifier module

Features:

Frequency: 2.7~3.5GHz

Saturated Output Power: P_{sat}≥40dBm

PowerGain: Gain≥28dB

Efficiency: η=45%(type)

Port Matching: Z_{in}/Z_{out}=50Ω

Description:

ANMI027035-P40 is an internal matching GaN power amplifier module, which adopts advanced co-planar internal matching MCM and thin film circuit technology. The typical working frequency range is 2.7~3.5GHz. This device can be used in different RF/Microwave system and subsystem.The high output power level, high efficiency and wide operating temperature range can make application very flexible.

Maximun Ratings (TC=25℃, Not recommended working under this condition):

	Symbol	Value	Unit
Voltage between source and drain	V_{DS}	40	V
Voltage between gate and source	V_{GS}	-5	V
Storage Temperature Range	T_{stg}	-65 to +175	℃
Drain and Source Channel Temperature	T_{ch}	175	℃

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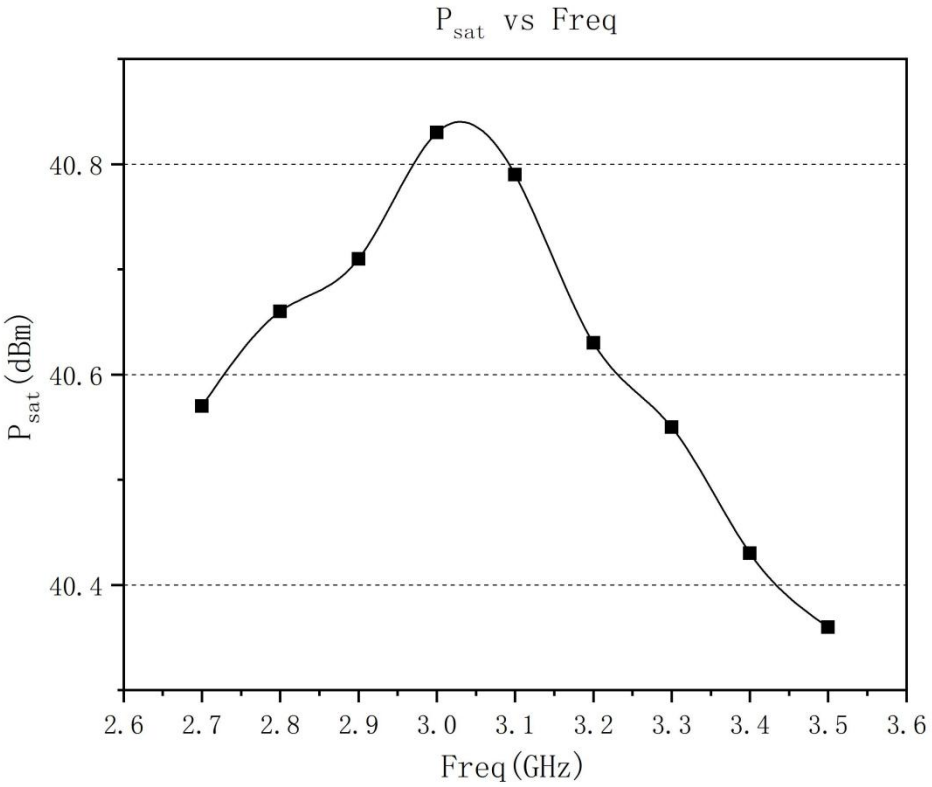
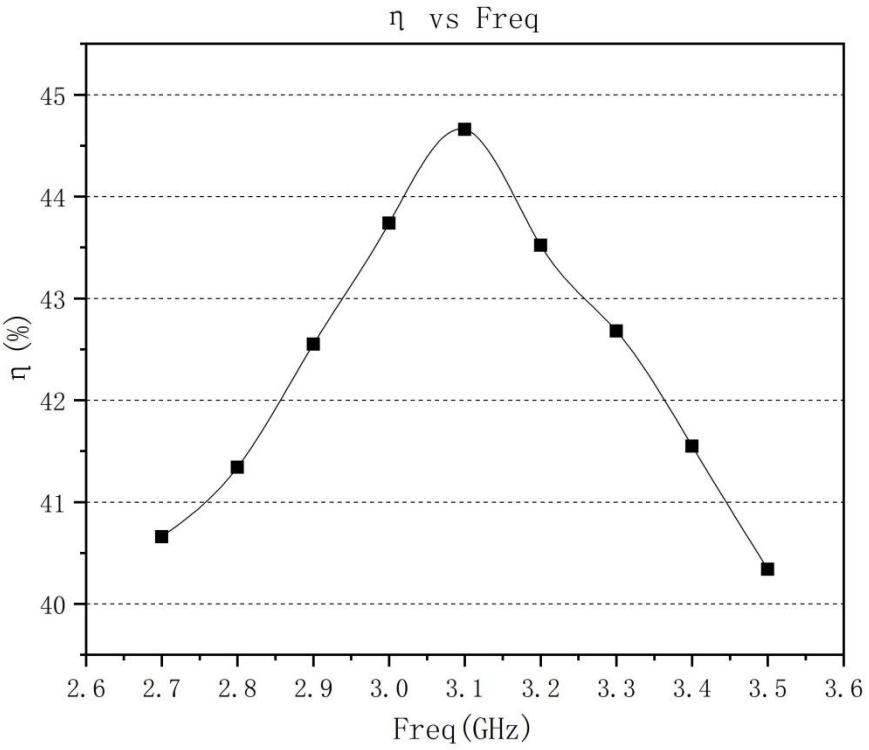
Electrical Characteristics:

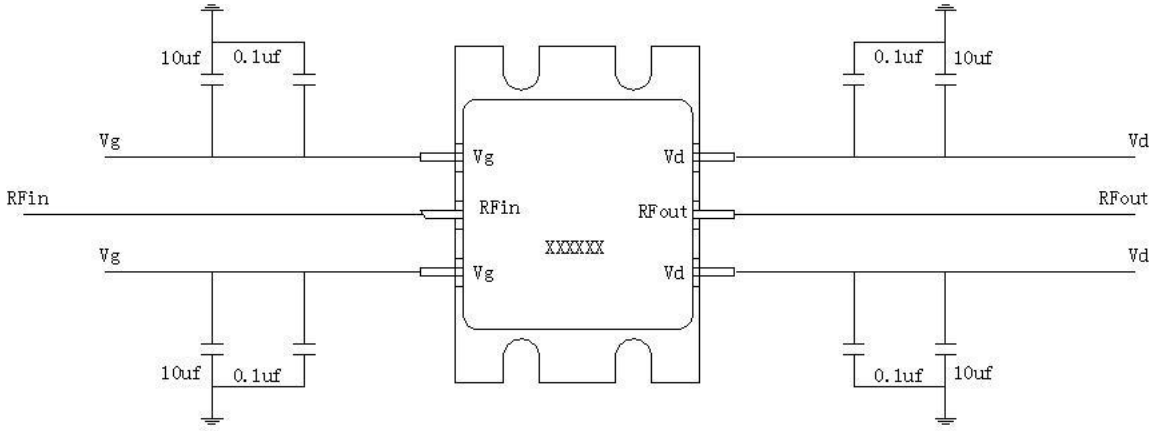
	Symbol	Test condition	Value			Unit
			Min	Typ	Max	
Drain Current	I_{dsr}	Vds=28V CW. Pin: 12dBm Freq: 2.7~3.5GHz	-	0.8	-	A
Saturated Output Power	P_{sat}		40	-	-	dBm
Gain	G_p		28	-	-	dB
Efficiency	η		-	45	-	%
Gain Flatness	ΔG		-0.8	-	+0.8	dB

Typical Curve:





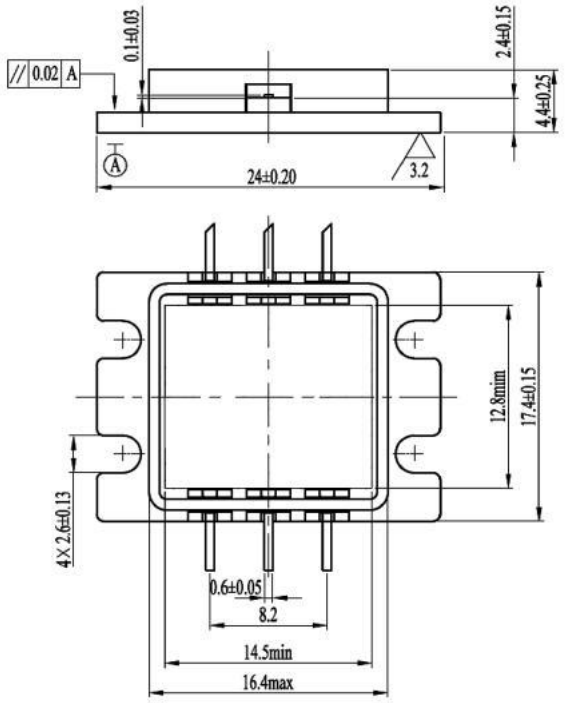
Application Circuit:



ESD Level:

ESD	Class III	2000V

Outline:



Precautions for use:

- Pay attention to drying transportation and storage.
- Pay attention to anti-static during chip use and assembly，and wear grounding anti-static bracelet.
- When powering up，first apply grid power then add leakage.